TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74AC153P, TC74AC153F, TC74AC153FN

#### **DUAL 4 – CHANNEL MULTIPLEXER**

The TC74AC153 is an advanced high speed CMOS DUAL 4-CHANNEL MULTIPLEXER fabricated with silicon gate and double-layer metal wiring  $C^2MOS$  technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

Each of these data  $(1C0 - 1C3, \ 2C0 - 2C3)$  is selected by the two address inputs A and B.

Separate strobe inputs  $(1\overline{G}, 2\overline{G})$  are provided for each of the two four-line sections.

The strobe input can be used to inhibit the data output; the output is fixed in low level unconditionally.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

#### FEATURES:

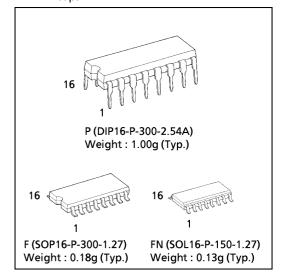
- High Speed······ $t_{pd}$  = 3.9ns(typ.) at  $V_{CC}$  = 5V
- Low Power Dissipation ··············· $I_{CC} = 8\mu A(Max.)$  at Ta = 25°C
- High Noise Immunity  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Symmetrical Output Impedance··· | I<sub>OH</sub> | = I<sub>OL</sub> = 24mA(Min.)

Capability of driving  $50\Omega$  transmission lines.

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- Balanced Propagation Delays ····· t<sub>pLH</sub> ≃ t<sub>pHL</sub>
- Wide Operating Voltage Range ···· V<sub>CC</sub> (opr) = 2V ~ 5.5V
- Pin and Function Compatible with 74F153

# (Note) The JEDEC SOP (FN) is not available in Japan.



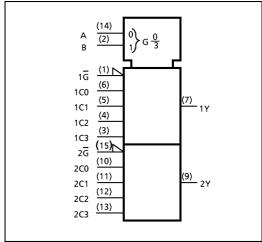
#### **PIN ASSIGNMENT** 1G 1 16 V<sub>CC</sub> 2G В 2 15 3 14 1C3 13 2C3 1C2 1C1 5 12 2C2 1C0 6 11 2C1 1Y 7 10 2C0 **GND** 8 2Y (TOP VIEW)

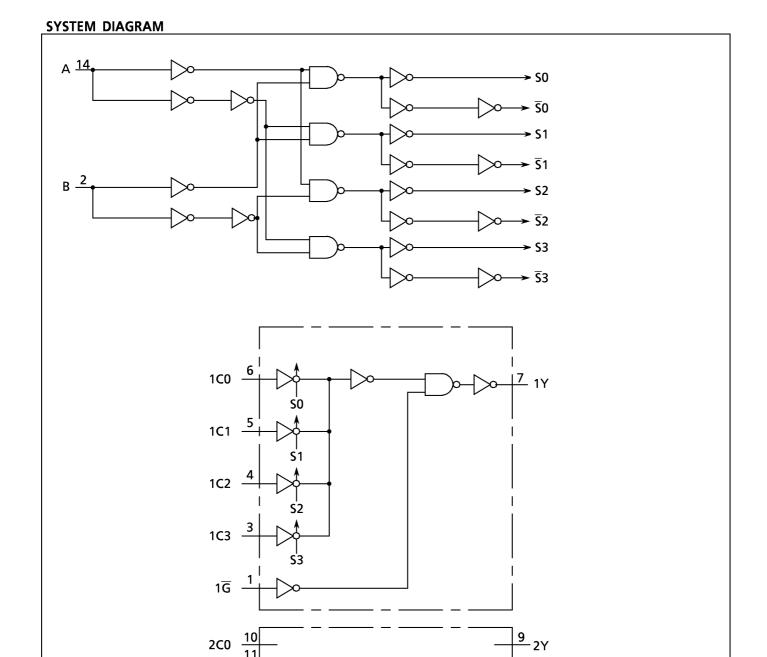
# TRUTH TABLE

	SELECT INPUTS		DATA I	NPUTS	STROBE	OUTPUT		
В	Α	C0	<b>C</b> 1	C2	C3	G	Υ	
Х	Х	Х	Х	Х	Х	Н	L	
L	L	L	Х	Х	Х	L	L	
L	L	Н	Х	X	Х	L	Н	
L	Ι	Х	L	Х	Х	L	L	
L	Ι	Х	Η	Χ	Х	L	Н	
Н	L	Х	Χ	L	Х	L	L	
Н	L	Х	Х	Η	Х	L	Н	
Н	Η	Х	Х	Х	Ĺ	Ĺ	Ĺ	
Н	Н	Х	Х	Х	Н	L	Н	

X: Don't Care

### IEC LOGIC SYMBOL





Same as above block

2C1

2C2

2C3

2G 15

12

13|

# **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	-0.5~7.0	٧
DC Input Voltage	V <sub>IN</sub>	$-0.5 \sim V_{CC} + 0.5$	>
DC Output Voltage	V <sub>OUT</sub>	−0.5~V <sub>CC</sub> + 0.5	٧
Input Diode Current	I <sub>IK</sub>	± 20	mA
Output Diode Current	I <sub>OK</sub>	± 50	mA
DC Output Current	I <sub>OUT</sub>	± 50	mA
DC V <sub>CC</sub> /Ground Current	I <sub>cc</sub>	± 100	mA
Power Dissipation	P <sub>D</sub>	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T <sub>stg</sub>	<b>−65~150</b>	°C

\*500mW in the range of Ta =  $-40^{\circ}$ C  $\sim$ 65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C should be applied up to 300mW.

#### RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2.0~5.5	٧
Input Voltage	VIN	0~V <sub>cc</sub>	>
Output Voltage	V <sub>OUT</sub>	0~V <sub>cc</sub>	٧
Operating Temperature	T <sub>opr</sub>	<b>−40~85</b>	°C
Input Rise and Fall Time	dt/dV	$0 \sim 100 \text{ (Vcc} = 3.3 \pm 0.3 \text{V)}$ $0 \sim 20 \text{ (Vcc} = 5 \pm 0.5 \text{V)}$	ns / V

### DC ELECTRICAL CHARACTERISTICS

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PARAMETER	SYMBOL	TEST CONDITION		V <sub>cc</sub>	Ι Τ	Ta = 25°C			Ta = −40~85°C	
FARAIVIETER	STIVIBUL			(V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High - Level Input Voltage	V <sub>IH</sub>			2.0 3.0 5.5	1.50 2.10 3.85	_ 	_ _	1.50 2.10 3.85	_ _	V
Low - Level Input Voltage	VIL			2.0 3.0 5.5		111	0.50 0.90 1.65	_ _ _	0.50 0.90 1.65	V
High - Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -50\mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	_ _	1.9 2.9 4.4	_ _	V
			$I_{OH} = -4mA$ $I_{OH} = -24mA$ $I_{OH} = -75mA*$	3.0 4.5 5.5	2.58 3.94 —			2.48 3.80 3.85		V
Low - Level Output Voltage	V <sub>OL</sub>	V <sub>1 N</sub> =	I <sub>OL</sub> = 50μA	2.0 3.0 4.5	_ _ _	0.0 0.0 0.0	0.1 0.1 0.1	_ _ _	0.1 0.1 0.1	V
		V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 12mA I <sub>OL</sub> = 24mA I <sub>OL</sub> = 75mA*	3.0 4.5 5.5	_ _ _	111	0.36 0.36 —	_ _ _	0.44 0.44 1.65	V
Input Leakage Current	I <sub>I N</sub>	$V_{IN} = V_{CC}$ or G	5.5	_	_	± 0.1	_	± 1.0		
Quiescent Supply Current $I_{CC}$ $V_{IN} = V_{CC}$ or GND			5.5	_	_	8.0	_	80.0	$\mu$ A	

<sup>\*</sup> This spec indicates the capability of driving  $50\Omega$  transmission lines. One output should be tested at a time for a 10ms maximum duration.

PARAMETER	SYMBOL	TEST CONDITION		-	Ta = 25°C		Ta = -40~85°C		UNIT
PARAIVIETER	STIVIBOL		V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
Propagation Delay Time (Cn-Y)	t <sub>pLH</sub> t <sub>pHL</sub>	I	3.3 ± 0.3 5.0 ± 0.5		7.6 5.0	14.5 9.0	1.0 1.0	16.5 10.3	
Propagation Delay Time (A, B-Y)	t <sub>pLH</sub> t <sub>pHL</sub>		3.3 ± 0.3 5.0 ± 0.5		10.5 6.6	20.5 10.5	1.0 1.0	23.4 12.0	ns
Propagation Delay Time $(\overline{G} - Y)$	t <sub>pLH</sub> t <sub>pHL</sub>		3.3 ± 0.3 5.0 ± 0.5		6.8 4.4	13.3 8.0	1.0 1.0	15.2 9.1	
Input Capacitance	C <sub>IN</sub>			_	5	10	_	10	
Power Dissipation Capacitance	C <sub>PD</sub> (1)		·	_	54	_	_	_	pF

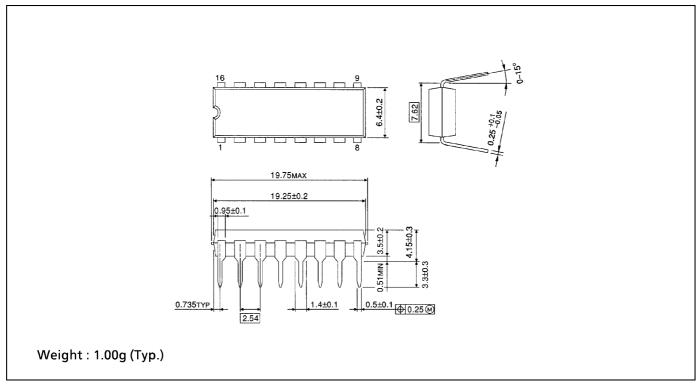
Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(opr.) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

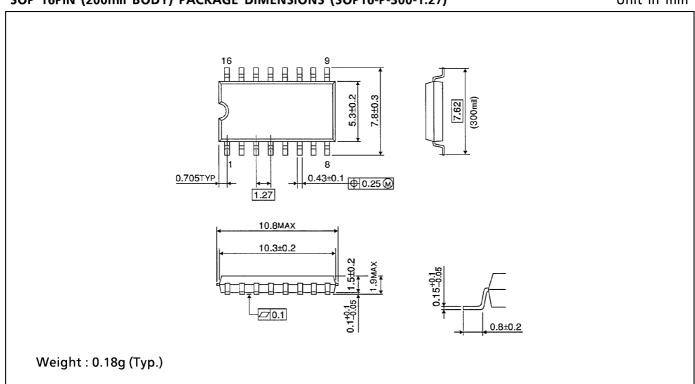
# DIP 16PIN PACKAGE DIMENSIONS (DIP16-P-300-2.54A)

Unit in mm



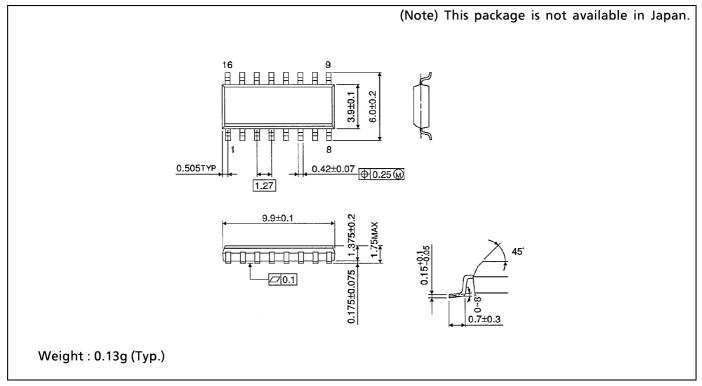
# SOP 16PIN (200mil BODY) PACKAGE DIMENSIONS (SOP16-P-300-1.27)

Unit in mm



# SOP 16PIN (150mil BODY) PACKAGE DIMENSIONS (SOL16-P-150 -1.27)

Unit in mm



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